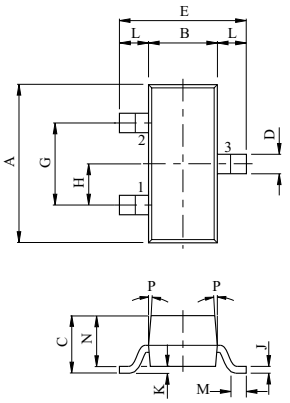
KTA1520S

EPITAXIAL PLANAR PNP TRANSISTOR

HIGH VOLTAGE APPLICATION.



DIM	MILLIMETERS
A	2.93±0.20
B	1.30+0.20/-0.15
C	1.30 MAX
D	0.45+0.15/-0.05
E	2.40+0.30/-0.20
G	1.90
H	0.95
J	0.13+0.10/-0.05
K	0.00 ~ 0.10
L	0.55
M	0.20 MIN
N	1.00+0.20/-0.10
P	7 °

1. EMITTER
2. BASE
3. COLLECTOR

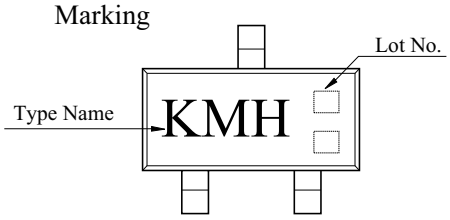
SOT-23

MAXIMUM RATING (Ta=25℃)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	-120	V
Collector-Emitter Voltage		V_{CEO}	-100	V
Emitter-Base Voltage		V_{EBO}	-5	V
Collector Current	DC	I_C	-1	A
	Pulse *	I_{CP}	-2	
Base Current		I_B	-200	mA
Collector Power Dissipation		P_C	150	mW
Junction Temperature		T_j	150	℃
Storage Temperature Range		T_{stg}	-55 ~ 150	℃

* Pulse Width = 300μS, Duty Cycle ≤2%.

Marking

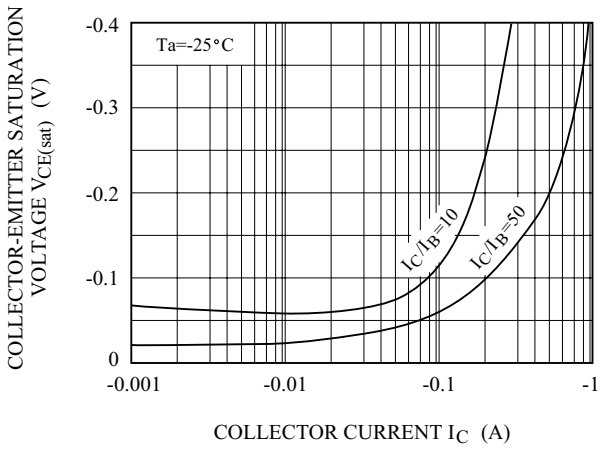


ELECTRICAL CHARACTERISTICS (Ta=25℃)

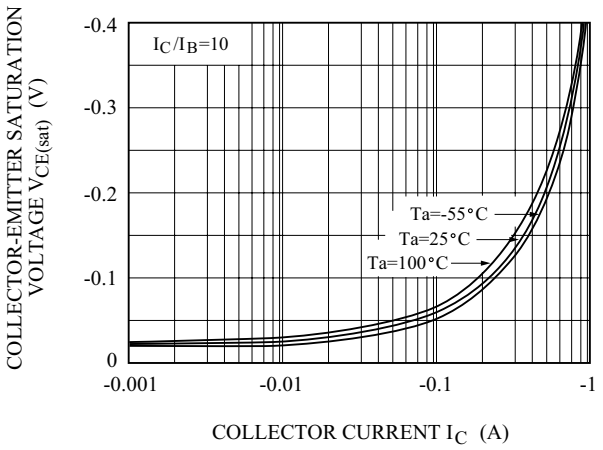
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=-100μA	-120	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=-10mA	-100	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=-100μA	-5	-	-	V
Collector Cut-Off Current	I_{CBO}	V_{CB}=-100V	-	-	-100	nA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=-4V	-	-	-100	nA
Collector-Emitter Cut-Off Current	I_{CES}	V_{CES}=-100V	-	-	-100	nA
Collector-Emitter Saturation Voltage **	$V_{CE(sat)}$ (1)	I_C=-250mA, I_B=-25mA	-	-	-0.2	V
	$V_{CE(sat)}$ (2)	I_C=-500mA, I_B=-50mA	-	-	-0.3	
Base-Emitter Saturation Voltage **	$V_{BE(sat)}$	I_C=-500mA, I_B=-50mA	-	-	-1.1	V
Base-Emitter Voltag	V_{BE}	V_{CE}=-5V, I_C=-1mA	-	-	-1.0	V
DC Current Gain **	h_{FE}(1)	V_{CE}=-5V, I_C=-1mA	100	-	-	
	h_{FE}(2)	V_{CE}=-5V, I_C=-250mA	100	-	-	
	h_{FE}(3)	V_{CE}=-5V, I_C=-500mA	100	-	300	
	h_{FE}(4)	V_{CE}=-5V, I_C=-1A	50	-	-	
Transition Frequency	f_T	V_{CE}=-10V, I_C=-50mA, f=100MHz	50	-	-	MHz
Collector Output Capacitance	C_{ob}	V_{CB}=-10V, f=1MHz	-	-	5	pF

** Pulse Width = 300μS, Duty Cycle ≤2%.

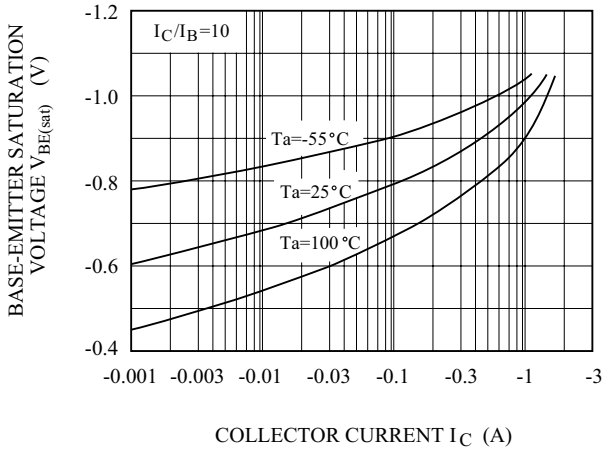
$V_{CE(sat)}$ - I_C



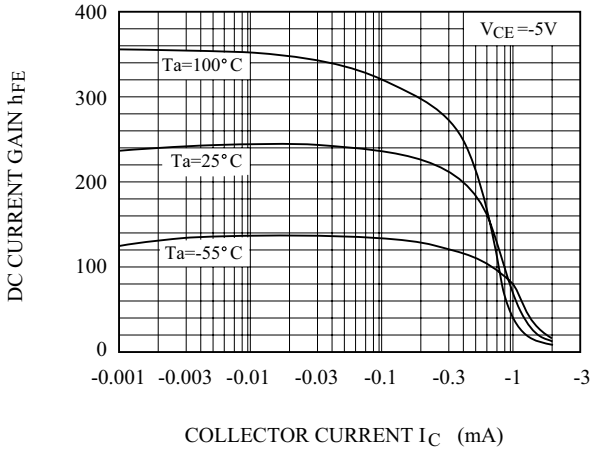
$V_{CE(sat)}$ - I_C



$V_{BE(sat)}$ - I_C



h_{FE} - I_C



I_C - V_{BE}